

N-Channel MOSFET

General Description

The WSD60N10GDN56 is the highest performance trench N-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WSD60N10GDN56 meet the RoHS and Green Product requirement, 100% E_{AS} guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% E_{AS} Guaranteed
- Green Device Available

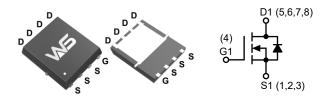
Product Summery

BV _{DSS}	R _{DS(ON)}	I _D
100V	8.5mΩ	60A

Applications

- Power Management in TV Converter.
- DC-DC Converter
- LED TV Back Light

DFN5X6-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage 100		V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current	60	۸
I _{DP}	Pulsed Drain Current	210	A
E _{AS}	Avalanche Energy, Single pulse	100	mJ
P _D @T _C =25°C	Total Power Dissipation	125	W
T _{STG}	Storage Temperature Range -55 to 150		°C
T_J	Operating Junction Temperature Range	-55 to 150	

Thermal Data

Symbol	Parameter	Тур.	Max.	Units
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		60	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		1.0	C/VV

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Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250μA	100			V
D	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =10A		8.5	10	m C
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V , I _D =10A		9.5	12	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_{D}=250\mu A$	1.0		2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V,T _J =25°C			1.0	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
Q_g	Total Gate Charge (10V)			49.9		
Q_{gs}	Gate-Source Charge	V_{DS} =50V , V_{GS} =10V , I_{D} =25A		6.5		nC
Q_{gd}	Gate-Drain Charge			12.4		
$T_{d(on)}$	Turn-On Delay Time			20.6		
T _r	Rise Time	V_{DD} =50V , V_{GS} =10V ,		5		no
$T_{d(off)}$	Turn-Off Delay Time	R _G =2.2Ω , I _D =25A		51.8		ns
T _f	Fall Time			9		
C _{iss}	Input Capacitance			2604		
C _{oss}	Output Capacitance	V_{DS} =50V , V_{GS} =0V , f = 1.0MHz		264		pF
C _{rss}	Reverse Transfer Capacitance			6.5		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
I _S	Continuous Source Current	√V _G =V _D =0V,Force Current			60	_
I _{SP}	Pulsed Source Current				210	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =12A , T _J =25°C			1.3	V
t _{rr}	Reverse Recovery Time	- I _F =12A , dl/dt=100A/μs , T _J =25°C		60.4		ns
Q _{rr}	Reverse Recovery Charge			106.1		nC

Note:

- 1. Calculated continuous current based on maximum allowable junction temperature.
- 2. Repetitive rating: pulse width limited by max. junction temperature.
- 3. $\ensuremath{\text{P}_{\text{D}}}$ is based on max. junction temperature, using junction-case thermal resistance.
- 4. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
- 5. V_{DD} =50V, R_G =25 Ω , L=0.3mH, starting T_J =25°C.



Typical Characteristics

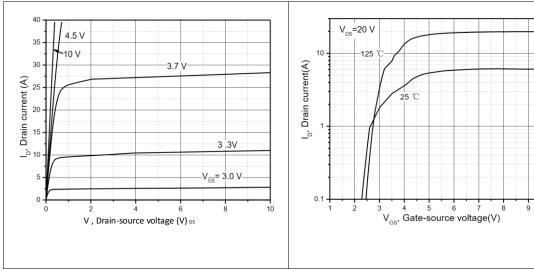


Figure 1, Typ. output characteristics

Figure 2, Typ. transfer characteristics Gate-source voltage(V) Ciss C, Capacitance(pF) 10° 40 Q_g, Gate charge(nC) , Drain-source voltage (V)

Figure 3, Typ. capacitances

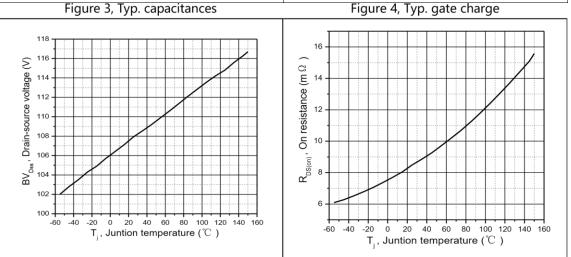
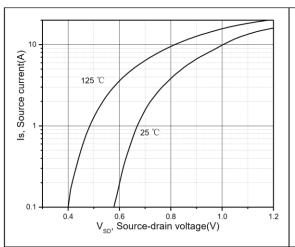


Figure 5, Drain-source breakdown voltage

Figure 6, Drain-source on-state resistance



Typical Characteristics (Cont.)



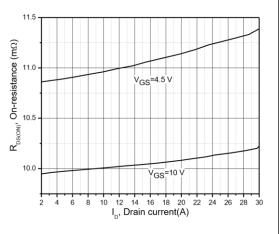


Figure 7, Forward characteristic of body diode

Figure 8, Drain-source on-state resistance

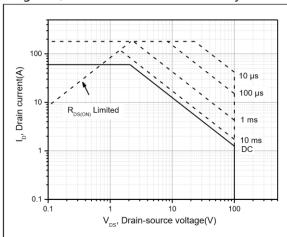
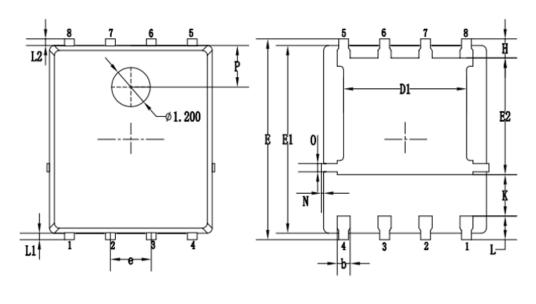
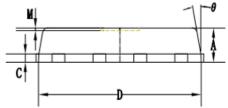


Figure 9, Safe operation area $T_C=25\,^{\circ}C$

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Packaging information





CVMDOLC		MILLIMETERS			
SYMBOLS	MIN.	NOM.	MAX.		
А	0.90	1.05	1.20		
b	0.35	0.40	0.50		
С	0.20	0.25	0.35		
D	4.90	5.05	5.20		
D1	3.72	3.82	3.92		
E	6.00	6.15	6.30		
E1	5.60	5.75	5.90		
E2	3.47	3.57	3.67		
е		1.27 BSC.			
Н	0.48	0.58	0.68		
K	1.17	1.27	1.37		
L	0.64	0.74	0.84		
L1/L2		0.20 REF.			
θ	8°	10°	12°		
М	,	0.08 REF.			
N	0	-	0.15		
0		0.25 REF.			
Р		1.28 REF.			



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